

**Amendments to the Specification:**

Please add the following new paragraph after the title on page 1:

CROSS REFERENCE TO RELATED APPLICATIONS

The present invention is a Divisional of prior application Serial No. 08/089,650 filed July 12, 1993, issued as U.S. Patent No. 6,458,200, which itself is a Continuation of application Serial No. 07/707,092 filed May 29, 1991, now abandoned.

Please replace the paragraph beginning at page 2, line 18, with the following rewritten paragraph:

In such TFTs, the current between the source 22 [22] and the drain 23 [23] (the source-to-drain current) can be controlled by applying a voltage to the gate contact 27 [27].

Please add the following new paragraph after the paragraph ending on line 5 of page 6:

Fig. 5 illustrates a method of manufacturing a thin film transistor in accordance with the present invention.